

EFW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Tetsuzo UEDA, et al.

Application No.: 10/812,416

Filed: March 30, 2004



Customer Number: 53080

Confirmation Number: 1264

Group Art Unit: 2811

Examiner: Crane, Sara W.

For: A 4H-POLYTYPE GALLIUM NITRIDE-BASED SEMICONDUCTOR DEVICE ON A 4H-POLYTYPE SUBSTRATE

Mail Stop Amendment
 Commissioner for Patents
 P.O. Box 1450
 Alexandria, VA 22313-1450

Dear Sir:

Transmitted herewith is an Amendment in the above-identified application.



No additional fee is required.



Applicant is entitled to small entity status under 37 CFR 1.27



Also attached: Copy of High-quality 4H-AIN of 4H-SiC(11-20) substrate by polytype matching dated 8/30/2003, which was filed in an IDS on 8/18/2004

The fee has been calculated as shown below:

	NO. OF CLAIMS	HIGHEST PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	FEE
Total Claims	10	49	0	\$50.00 =	\$0.00
Independent Claims	2	5	0	\$200.00 =	\$0.00
Multiple dependent claims newly presented					\$0.00
Fee for extension of time					\$0.00
					\$0.00
Total of Above Calculations					\$0.00

Please charge my Deposit Account No. 500417 in the amount of \$0.00. An additional copy of this transmittal sheet is submitted herewith.

The Commissioner is hereby authorized to charge payment of any fees associated with this communication or credit any overpayment, to Deposit Account No. 500417, including any filing fees under 37 CFR 1.16 for presentation of extra claims and any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

McDERMOTT WILL & EMERY LLP

Michael E. Fogarty
 Registration No. 36,139

Please recognize our Customer No. 53080 as our
 correspondence address.

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 Date: July 13, 2007



Docket No.: 074968-0011

PATENT

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Tetsuzo UEDA, et al.	:	Confirmation Number: 1264
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AMENDMENT

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In response to the Office Action dated April 13, 2007, having a three-month shortened statutory period for response set to expire July 13, 2007, please amend the above identified application as follows: